

NPN/PNP POWER DARLINGTON TRANSISTOR ARRAY

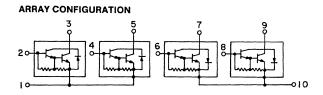
D76FY2D

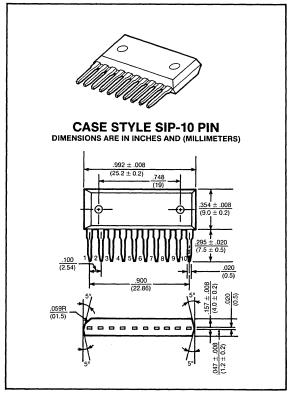
80 VOLTS 2 AMP, 4.0 WATTS

Designed for high power switching applications, hammer drive, pulse motor drive and inductive load drive applications.

Features:

- High reliability small-sized available (4 in 1)
- Epoxy single-inline package (10 pin)
- Zener diode included between collector and base
- High collector power dissipation: PD = 4.0W @ TA = 25°C (Four device action)
- High collector current: IC = ±2A (Max.)
- High DC current gain:
 hFE = 2000 (Min.) @ VCE = ±2V, IC = ±1A





maximum ratings (T_A = 25°C) (unless otherwise specified)

RATING	SYMBOL	D76FY2D	UNITS
Collector-Emitter Voltage	V _{CEO}	80	Volts
Collector-Base Voltage	V _{CBO}	80	Volts
Emitter Base Voltage	V _{EBO}	8	Volts
Collector Current — Continuous Peak	I _C	2 3	А
Base Current — Continuous	I _B	0.5	A
Collector Power Dissipation (One Device Action, T _A = 25°C)	P _D	2.0	Watts
Collector Power Dissipation (Four Device Action, T _A = 25°C)	P _D	4.0	Watts
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-55 to +150	°C

thermal characteristics

Thermal Resistance, Junction to Ambient (Four Device Action)	ΣR _{θJA}	31.3	°C/W
Maximum Lead Temperature for Soldering Purpose: 1/8" from Case for 5 Seconds	ΤĻ	260	°C

electrical characteristics (T_A = 25°C) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
ff characteristics					
Collector-Emitter Breakdown Voltage (I _C = 10mA, I _B = 0)	V _{BR(CEO)}	80	_	_	Volts
Collector-Base Breakdown Voltage (I _C = 1mA, I _E = 0)	V _{BR(CBO)}	80	_		Volts
Collector Cutoff Current (V _{CB} = 80V, I _E = 0)	ІСВО	_	_	10	μΑ
Collector Cutoff Current (V _{CE} = 80V, I _B = 0)	ICEO		_	50	μΑ
Emitter Cutoff Current (V _{EB} = 8V, I _C = 0)	I _{EBO}		_	4	mA

on characteristics

DC Current Gain (I _C = 1A, V _{CE} = 1V)	h _{FE}	2000		_	_
Collector-Emitter Saturation Voltage (I _C = 1A, I _B = 1mA)	V _{CE(sat)}		_	1.5	Volts
Base-Emitter Saturation Voltage (I _C = 1A, I _B = 1mA)	V _{BE(sat)}	<u> </u>		2.0	Volts

switching characteristics

Turn-on Time	V _{CC} = 30V	t _{on}	-	0.4	_	μS
Storage Time	I _{B1} = -I _{B2} = 1mA	t _{stg}		4.0		
Fall Time	Duty Cycle = 1%	t _f		0.6	_	

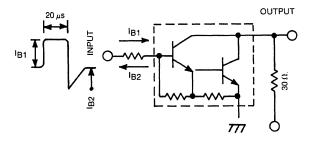


FIG. 1 SWITCHING TIME TEST CIRCUIT